

74AHC1G125; 74AHCT1G125

Bus buffer/line driver; 3-state

Product data sheet

1. General description

74AHC1G125 and 74AHCT1G125 are high-speed Si-gate CMOS devices. They provide one non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (\overline{OE}). A HIGH at \overline{OE} causes the output to assume a high-impedance OFF-state.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options
- ESD protection:
 - ◆ HBM JESD22-A114E: exceeds 2000 V
 - ◆ MM JESD22-A115-A: exceeds 200 V
 - ◆ CDM JESD22-C101C: exceeds 1000 V
- Specified from -40°C to $+125^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package				Version
	Temperature range	Name	Description		
74AHC1G125GW	-40°C to $+125^{\circ}\text{C}$	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm		SOT353-1
74AHCT1G125GW					
74AHC1G125GV	-40°C to $+125^{\circ}\text{C}$	SC-74A	plastic surface-mounted package; 5 leads		SOT753
74AHCT1G125GV					

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state

Inputs		Output
OE	A	Y
L	L	L
L	H	H
H	X	Z

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit	
V _{CC}	supply voltage		-0.5	+7.0	V	
V _I	input voltage		-0.5	+7.0	V	
I _{IK}	input clamping current	V _I < -0.5 V	-20	-	mA	
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	[1]	-	±20	mA
I _O	output current	-0.5 V < V _O < V _{CC} + 0.5 V	-	±25	mA	
I _{CC}	supply current		-	75	mA	
I _{GND}	ground current		-75	-	mA	
T _{stg}	storage temperature		-65	+150	°C	
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[2]	-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For both TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC1G125			74AHCT1G125			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V _I	input voltage		0	-	5.5	0	-	5.5	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 3.3 V ± 0.3 V	-	-	100	-	-	-	ns/V
		V _{CC} = 5.0 V ± 0.5 V	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
For type 74AHC1G125										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = −50 µA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = −50 µA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = −50 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = −4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I _O = −8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 50 µA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 µA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I _{OZ}	OFF-state output current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	0.25	-	2.5	-	10	µA
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	-	10	-	40	µA
C _I	input capacitance		-	1.5	10	-	10	-	10	pF
For type 74AHCT1G125										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = −50 µA	4.4	4.5	-	4.4	-	4.4	-	V
V _{OL}	LOW-level output voltage	I _O = −8.0 mA	3.94	-	-	3.8	-	3.70	-	V
		I _O = 50 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V

Table 7. Static characteristics ...continued
Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I _{OZ}	OFF-state output current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	0.25	-	2.5	-	10	μA
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	-	10	-	40	μA
ΔI _{CC}	additional supply current	per input pin; V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C _I	input capacitance		-	1.5	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; t_r = t_f = ≤ 3.0 ns. For test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
For type 74AHC1G125										
t _{pd}	propagation delay	A to Y; see Figure 5	[1]							
		V _{CC} = 3.0 V to 3.6 V	[2]							
		C _L = 15 pF	-	4.7	8.0	1.0	9.5	1.0	11.5	ns
		C _L = 50 pF	-	6.6	11.5	1.0	13.0	1.0	14.5	ns
		V _{CC} = 4.5 V to 5.5 V	[3]							
		C _L = 15 pF	-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF	-	4.8	7.5	1.0	8.5	1.0	9.5	ns
t _{en}	enable time	OE to Y; see Figure 6	[1]							
		V _{CC} = 3.0 V to 3.6 V	[2]							
		C _L = 15 pF	-	5.0	8.0	1.0	9.5	1.0	11.5	ns
		C _L = 50 pF	-	6.9	11.5	1.0	13.0	1.0	14.5	ns
		V _{CC} = 4.5 V to 5.5 V	[3]							
		C _L = 15 pF	-	3.6	5.1	1.0	6.0	1.0	6.5	ns
		C _L = 50 pF	-	4.9	7.5	1.0	8.5	1.0	9.5	ns
t _{dis}	disable time	OE to Y; see Figure 6	[1]							
		V _{CC} = 3.0 V to 3.6 V	[2]							
		C _L = 15 pF	-	6.0	9.7	1.0	11.5	1.0	12.5	ns
		C _L = 50 pF	-	8.3	13.2	1.0	15.0	1.0	16.5	ns
		V _{CC} = 4.5 V to 5.5 V	[3]							
		C _L = 15 pF	-	4.1	6.8	1.0	8.0	1.0	8.5	ns
		C _L = 50 pF	-	5.7	8.8	1.0	10.0	1.0	11.0	ns

Table 8. Dynamic characteristics ...continuedGND = 0 V; $t_r = t_f = \leq 3.0$ ns. For test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C_{PD}	power dissipation capacitance	per buffer; $C_L = 50$ pF; $f = 1$ MHz; $V_I = GND$ to V_{CC}	[4]	-	9	-	-	-	-	pF
For type 74AHCT1G125										
t_{pd}	propagation delay	A to Y; see Figure 5 $V_{CC} = 4.5$ V to 5.5 V	[1] [3]							
		$C_L = 15$ pF	-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		$C_L = 50$ pF	-	4.8	7.5	1.0	8.5	1.0	9.5	ns
t_{en}	enable time	\overline{OE} to Y; see Figure 6 $V_{CC} = 4.5$ V to 5.5 V	[1] [3]							
		$C_L = 15$ pF	-	3.9	5.1	1.0	6.0	1.0	6.5	ns
		$C_L = 50$ pF	-	5.1	7.5	1.0	8.5	1.0	9.5	ns
t_{dis}	disable time	\overline{OE} to Y; see Figure 6 $V_{CC} = 4.5$ V to 5.5 V	[1] [3]							
		$C_L = 15$ pF	-	4.5	6.8	1.0	8.0	1.0	8.5	ns
		$C_L = 50$ pF	-	6.1	8.8	1.0	10.0	1.0	11.0	ns
C_{PD}	power dissipation capacitance	per buffer; $C_L = 50$ pF; $f = 1$ MHz; $V_I = GND$ to V_{CC}	[4]	-	11	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} . t_{en} is the same as t_{PZL} and t_{PZH} . t_{dis} is the same as t_{PLZ} and t_{PHZ} .[2] Typical values are measured at $V_{CC} = 3.3$ V.[3] Typical values are measured at $V_{CC} = 5.0$ V.[4] C_{PD} is used to determine the dynamic power dissipation P_D (μ W).

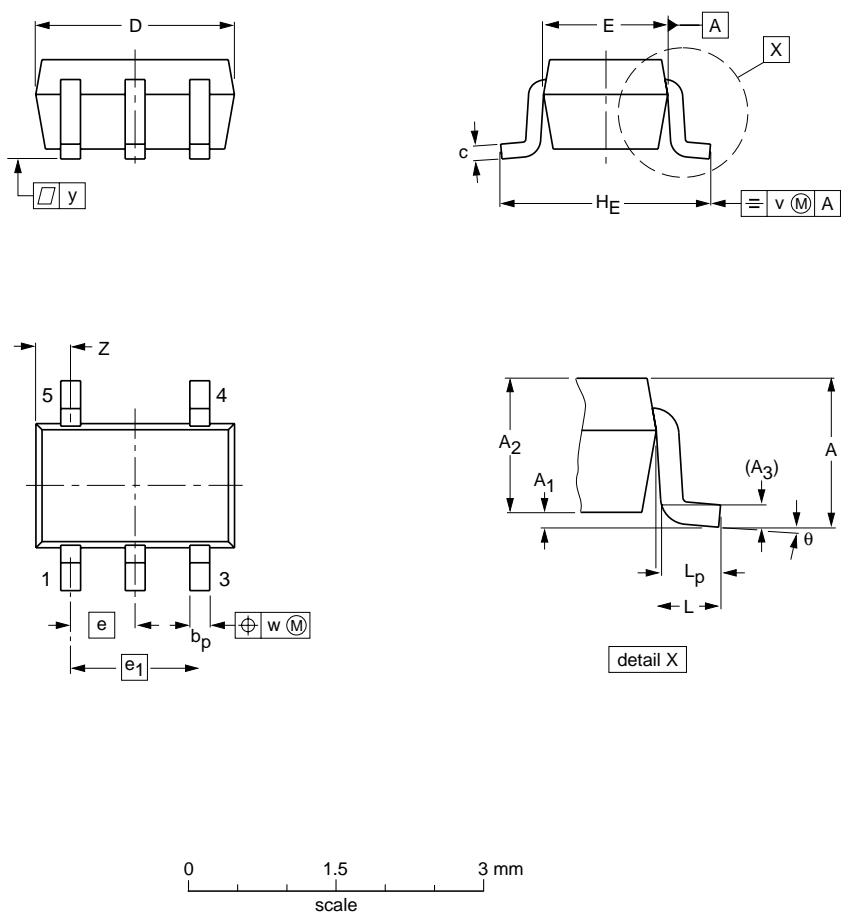
$$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

 f_i = input frequency in MHz; f_o = output frequency in MHz; C_L = output load capacitance in pF; V_{CC} = supply voltage in Volts.

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	H _E	L	L _p	v	w	y	Z ⁽¹⁾	theta
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

Note

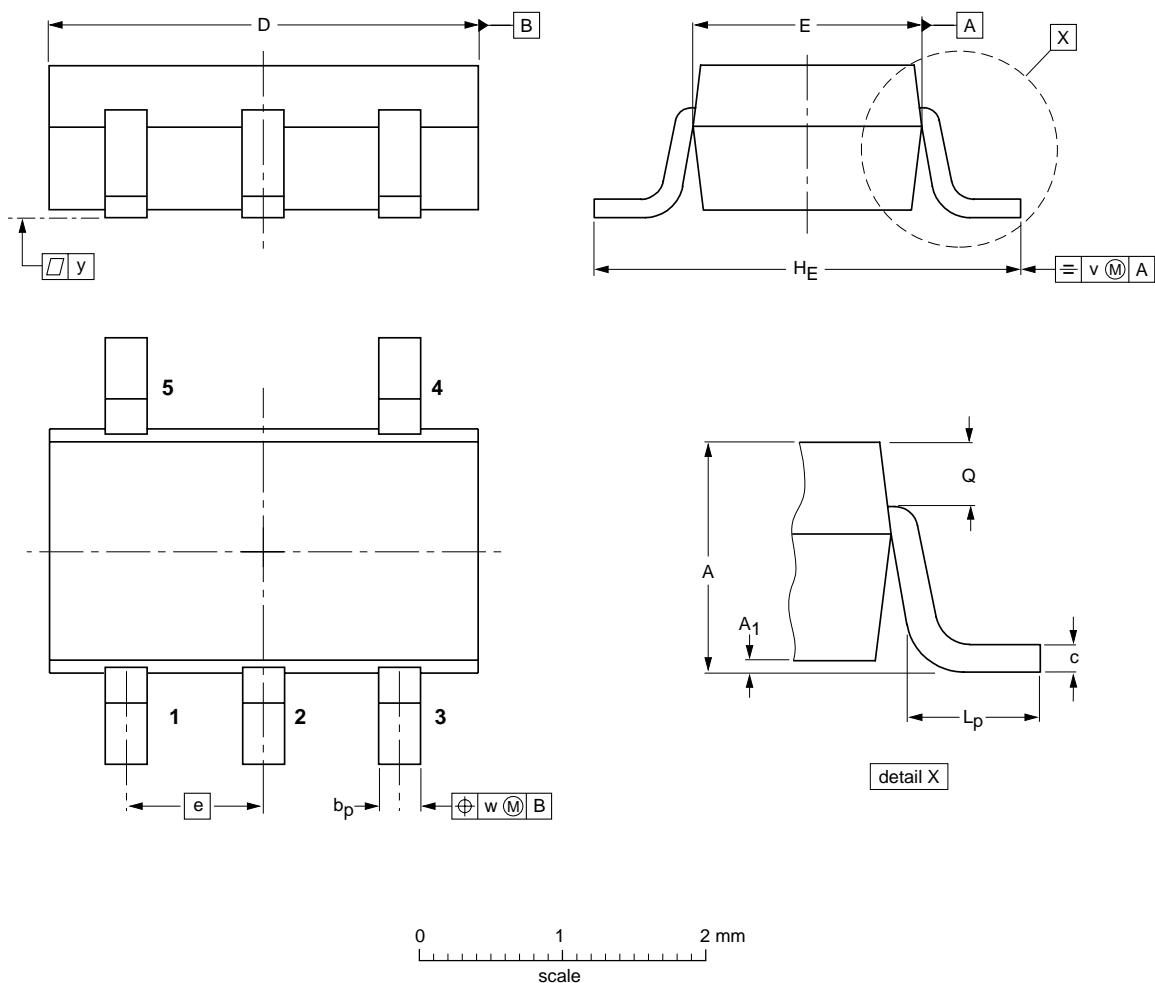
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	
	IEC	JEDEC	JEITA			
SOT353-1		MO-203	SC-88A			

Fig 8. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

**DIMENSIONS (mm are the original dimensions)**

UNIT	A	A ₁	b _p	c	D	E	e	H _E	L _p	Q	v	w	y
mm	1.1 0.9	0.100 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	
	IEC	JEDEC	JEITA			
SOT753			SC-74A			

Fig 9. Package outline SOT753 (SC-74A)